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ON Semiconductor 2N6338

For any questions, you can email us directly: sales@integrated-circuit.com

2N6338, 2N6341

High-Power NPN Silicon Transistors

... designed for use in industrial-military power amplifier and switching circuit applications.

• High Collector-Emitter Sustaining Voltage -

$$V_{CEO(sus)} = 100 \text{ Vdc (Min)} - 2N6338$$

= 150 Vdc (Min) - 2N6341

• High DC Current Gain -

$$h_{FE} = 30 - 120 @ I_C = 10 Adc$$

= 12 (Min) @ $I_C = 25 Adc$

• Low Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 1.0 \text{ Vdc (Max)} @ I_C = 10 \text{ Adc}$$

• Fast Switching Times @ I_C = 10 Adc

 $t_r = 0.3 \text{ ms (Max)}$

 $t_s = 1.0 \text{ ms (Max)}$

 $t_f = 0.25 \text{ ms (Max)}$

• Pb-Free Packages are Available

*MAXIMUM RATINGS

| Rating | Symbol | 2N6338 | 2N6341 | Unit | |
|--|-----------------------------------|-------------|--------|-----------|--|
| Collector-Base Voltage | V _{CB} | CB 120 180 | | Vdc | |
| Collector-Emitter Voltage | V _{CEO} | 100 150 | | Vdc | |
| Emitter-Base Voltage | V _{EB} | 6.0 | | Vdc | |
| Collector Current Continuous Peak | I _C | 25 50 | | Adc | |
| Base Current | I _B | 10 | | Adc | |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 200 1.14 | | W W/°C | |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +200 | | °C | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--------------------------------------|----------------------|-------|------|
| Thermal Resistance, Junction to Case | θ_{JC} | 0.875 | °C/W |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. *Indicates JEDEC Registered Data.



ON Semiconductor®

http://onsemi.com

25 AMPERE **POWER TRANSISTORS NPN SILICON**



TO-204AA **CASE 1-07**

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|-----------------------|------------------|
| 2N6338 | TO-204AA | 100 Units / Tray |
| 2N6338G | TO-204AA (Pb-Free) | 100 Units / Tray |
| 2N6341 | TO-204AA | 100 Units / Tray |
| 2N6341G | TO-204AA (Pb-Free) | 100 Units / Tray |

Datasheet of 2N6338 - TRANS NPN 100V 25A TO-3

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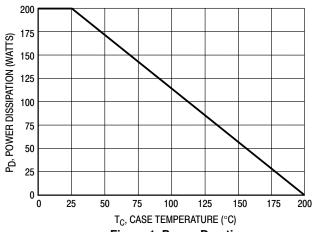


Figure 1. Power Derating

*ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit | |
|--|----------------------|----------------|---------------|--------------|--|
| OFF CHARACTERISTICS | | | | | |
| Collector–Emitter Sustaining Voltage (1) 2N6338 $(I_C = 50 \text{ mAdc}, I_B = 0)$ 2N6341 | OLO(sus) | 100 150 | | Vdc | |
| | | - - | 50 50 | μAdc | |
| Collector Cutoff Current $(V_{CE} = Rated \ V_{CEO}, \ V_{EB(off)} = 1.5 \ Vdc)$ $(V_{CE} = Rated \ V_{CEO}, \ V_{EB(off)} = 1.5 \ Vdc, \ T_{C} = 150^{\circ}C)$ | I _{CEX} | - - | 10 1.0 | μAdc mAdc | |
| Collector Cutoff Current (V _{CB} = Rated V _{CB} , I _E = 0) | I _{CBO} | - | 10 | μAdc | |
| Emitter Cutoff Current (V _{BE} = 6.0 Vdc, I _C = 0) | I _{EBO} | - | 100 | μAdc | |
| ON CHARACTERISTICS (1) | | | | • | |
| DC Current Gain) $ \begin{aligned} &(I_C=0.5 \text{ Adc, } V_{CE}=2.0 \text{ Vdc}) \\ &(I_C=10 \text{ Adc, } V_{CE}=2.0 \text{ Vdc}) \\ &(I_C=25 \text{ Adc, } V_{CE}=2.0 \text{ Vdc}) \end{aligned} $ | h _{FE} | 50 30 12 | - 120 - | - | |
| Collector Emitter Saturation Voltage (I _C = 10 Adc, I _B = 1.0 Adc) (I _C = 25 Adc, I _B = 2.5 Adc) | V _{CE(sat)} | | 1.0 1.8 | Vdc | |
| Base–Emitter Saturation Voltage (I _C = 10 Adc, I _B = 1.0 Adc) (I _C = 25 Adc, I _B = 2.5 Adc) | V _{BE(sat)} | _ _ | 1.8 2.5 | Vdc | |
| Base–Emitter On Voltage (I _C = 10 Adc, V _{CE} = 2.0 Vdc) | V _{BE(on)} | - | 1.8 | Vdc | |
| DYNAMIC CHARACTERISTICS | | | | | |
| Current-Gain - Bandwidth Product (2) (I _C = 1.0 Adc, V _{CE} = 10 Vdc, f _{test} = 10 MHz) | f _T | 40 | _ | MHz | |
| Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz) | C _{ob} | - | 300 | pF | |
| SWITCHING CHARACTERISTICS | | | | | |
| Rise Time ($V_{CC} \approx 80 \text{ Vdc}$, $I_C = 10 \text{Adc}$, $I_{B1} = 1.0 \text{ Adc}$, $V_{BE(off)} = 6.0 \text{ Vdc}$) | t _r | - | 0.3 | μs | |
| Storage Time ($V_{CC} \approx 80$ Vdc, $I_C = 10$ Adc, $I_{B1} = I_{B2} = 1.0$ Adc) | t _s | - | 1.0 | μs | |
| Fall Time ($V_{CC} \approx 80$ Vdc, $I_C = 10$ Adc, $I_{B1} = I_{B2} = 1.0$ Adc) | t _f | - | 0.25 | μs | |

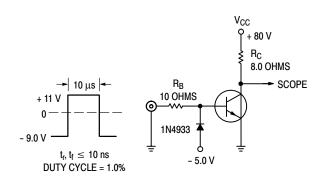
^{*}Indicates JEDEC Registered Data.
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

⁽²⁾ $f_T = |h_{fe}| \bullet f_{test}$.

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NOTE: For information on Figures 3 and 6, R_B and R_C were varied to obtain desired test conditions.

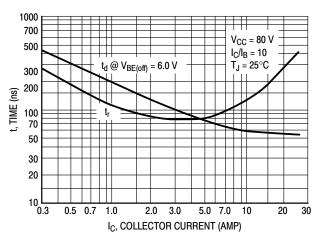
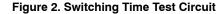


Figure 3. Turn-On Time



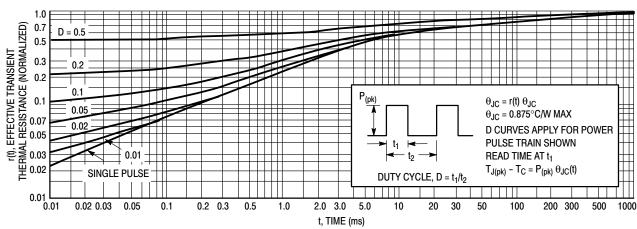


Figure 4. Thermal Response

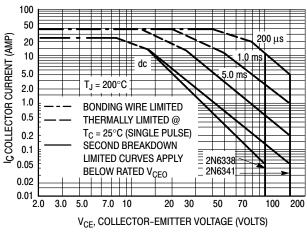


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_{C} – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 200^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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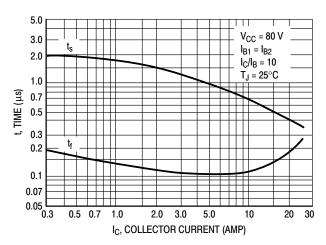


Figure 6. Turn-Off Time

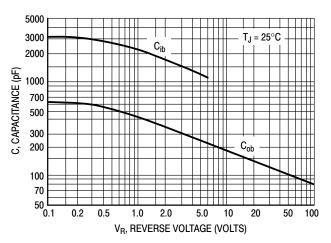


Figure 7. Capacitance



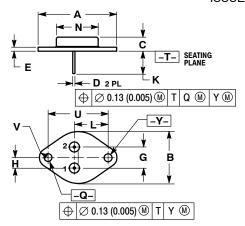
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PACKAGE DIMENSIONS

TO-204AA (TO-3 CASE 1-07 ISSUE Z



NOTES.

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M. 1982.
- 2. CONTROLLING DIMENSION: INCH
- 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

| | INCHES | | CHES MILLIMET | | |
|-----|-----------|-------|-----------------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 1.550 REF | | 39.37 | REF | |
| В | | 1.050 | | 26.67 | |
| С | 0.250 | 0.335 | 6.35 | 8.51 | |
| D | 0.038 | 0.043 | 0.97 | 1.09 | |
| E | 0.055 | 0.070 | 1.40 | 1.77 | |
| G | 0.430 BSC | | 10.92 BSC | | |
| Н | 0.215 BSC | | 5.46 BSC | | |
| K | 0.440 | 0.480 | 11.18 | 12.19 | |
| L | 0.665 BSC | | 16.89 BSC | | |
| N | | 0.830 | | 21.08 | |
| Q | 0.151 | 0.165 | 3.84 | 4.19 | |
| U | 1.187 BSC | | 30.15 BSC | | |
| ٧ | 0.131 | 0.188 | 3.33 | 4.77 | |

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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